

[MoA1] 2D Materials - I

Session Date	July 13 (Mon.), 2026
Session Time	11:15–12:30
Session Room	Room A (Baekrok Hall A, 1F)
Session Chairs	Dr. Benjamin Groven (IMEC, Belgium), Prof. Kerstin Volz (Philipps–University Marburg, Germany)

[MoA1–1] [Invited]

11:15–11:45

From MOCVD to AI-Driven Metrology: Enabling Scalable Production and Quality Control of Wafer-Scale 2D Semiconductors

Xiaotian Zhang, Suzhou Laboratory, China

[MoA1–2] [Invited]

11:45–12:15

Scalable MOVPE van der Waals Epitaxy of hBN for III–Nitride Devices: From Mixed 2D/3D Heterostructures to RGB Micro–LEDs and Deep–UV LEDs

Suresh Sundaram^{1,2}, Phuong Vuong^{1,2,3}, May Tran Thi², Ashuthosh Srivastava^{1,2}, Tarik Moudakir⁴, Simon Gautier⁴, Paul L. Voss^{1,2}, Jean Paul Salvestrini^{1,2}, and Abdallah Ougazzaden^{1,2}, ¹Georgia Tech–Europe, France, ²Georgia Tech–CNRS IRL 2958, France, ³Georgia Institute of Technology, USA, ⁴Institut Lafayette, France

[MoA1–3]

12:15–12:30

MOCVD Growth of Suspended hBN on GaN Nano–Needles for Analog Memristive Switching via Geometric Filament Confinement

Seokho Moon¹, Jaesub Song², Odongo Francis Ngome Okello¹, Adrien Rousseau³, Semi Im², Jawon Kim², Inyong Hwang², Changuk Ji², Jinho Byun², Jiye Kim², Junyoung Choi², Hyunjeong Kwak², Seyoung Kim², Bernard Gil³, Guillaume Cassabois³, Si–Young Choi², and Jong Kyu Kim², ¹Ajou University, Korea, ²Pohang University of Science and Technology, Korea, ³Universite de Montpellier, France